

MBR545

Features

- Metal of silicon rectifier, majority carrier conduction
- Guard ring for transient protection
- Low power loss high efficiency
- High surge capacity, High current capability

Maximum Ratings

- Operating Temperature: -55°C to +125°C
- Storage Temperature: -55°C to +150°C

Microsemi Catalog Number	Device Marking	Maximum Recurrent Peak Reverse Voltage	Maximum RMS Voltage	Maximum DC Blocking Voltage
MBR545	MBR545	45V	31.5V	45V

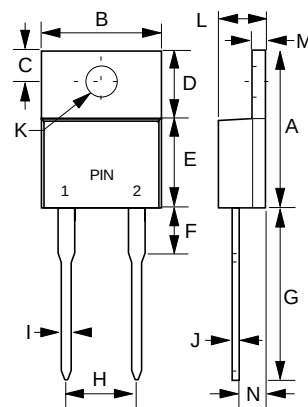
Electrical Characteristics @ 25°C Unless Otherwise Specified

Average Forward Current	$I_{F(AV)}$	5A	$T_C = 95^\circ\text{C}$
Peak Forward Surge Current	I_{FSM}	150A	8.3ms, half sine
Maximum Forward Voltage Drop Per Element	V_F	.60V	$I_{FM} = 5 \text{ A mper}$ $T_J = 25^\circ\text{C}$
Maximum DC Reverse Current At Rated DC Blocking Voltage	I_R	0.1mA 15mA	$T_J = 25^\circ\text{C}$ $T_J = 100^\circ\text{C}$
Typical Junction Capacitance	C_J	350pF	Measured at 1.0MHz, $V_R = 4.0\text{V}$

*Pulse test: Pulse width 300 μsec , Duty cycle 2%

5 Amp Schottky Barrier Rectifier 45 Volts

TO-220AC



DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	.560	.625	14.22	15.88	
B	.380	.420	9.65	10.67	
C	.100	.135	2.54	3.43	
D	.230	.270	5.84	6.86	
E	.380	.420	9.65	10.67	
F	---	.250	---	6.35	
G	.500	.580	12.70	14.73	
H	.190	.210	4.83	5.33	
I	.020	.045	0.51	1.14	
J	.012	.025	0.30	0.64	
K	.139	.161	3.53	4.09	Ø
L	.140	.190	3.56	4.83	
M	.045	.055	1.14	1.40	
N	.080	.115	2.03	2.92	

[查询"MBR545"供应商](#)

FIG.1 - FORWARD CURRENT DERATING CURVE

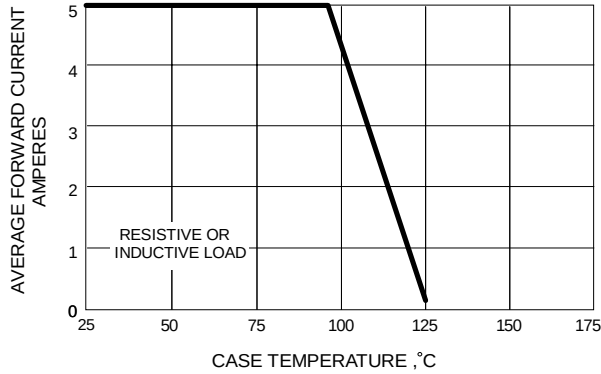


FIG.2 - MAXIMUM NON-REPETITIVE SURGE CURRENT

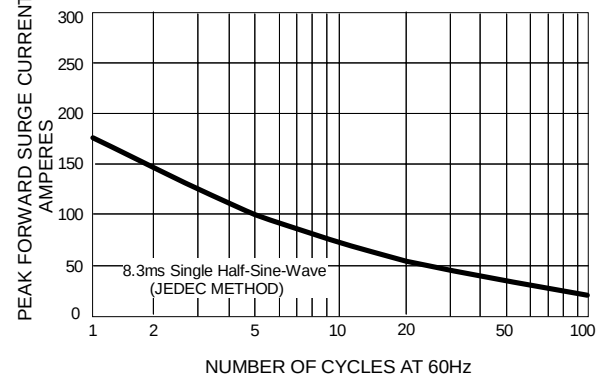


FIG.3 - TYPICAL REVERSE CHARACTERISTICS

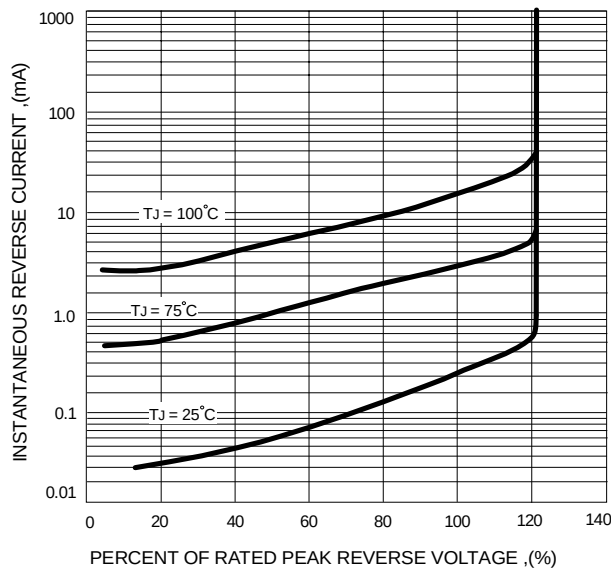


FIG.4 - TYPICAL FORWARD CHARACTERISTICS

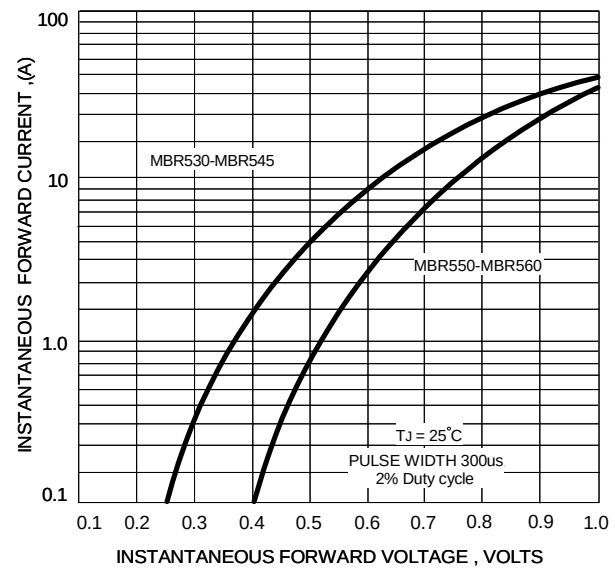


FIG.5 - TYPICAL JUNCTION CAPACITANCE

